IN THE CLAIMS:

1. (Currently Amended) In the fabrication of integrated circuit (IC) structures, a method for forming a structure resistant to ozone stripping, the method comprising:

forming a first electrically conducting layer from indium tin oxide (ITO);

forming an ozone resistant barrier overlying the first
electrically conducting layer from a material selected from the group
including Ta, Ti, TaN, Al, Al compounds, tungsten, and copper; and,
forming a metal layer overlying the ozone resistive barrier.

- 2. (Cancelled)
- 3. (Cancelled)
- 4. (Original) The method of claim 1 wherein forming a metal layer overlying the ozone resistant barrier includes forming a reflective metal layer from Al.



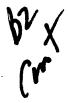
- 5. (Original) The method of claim 4 wherein forming a metal layer overlying the ozone resistant barrier includes forming a layer of Al having a thickness of greater than 1000 Å.
- 6. (Original) The method of claim 1 in which a reflective liquid crystal display (LCD) IC structure is formed;

wherein forming a first electrically conducting layer includes forming an electrode; and,

wherein forming a metal layer overlying the ozone resistant barrier includes forming an LCD reflector.

7. (Original) The method of claim 1 in which a busline IC structure is formed; and,

wherein forming a metal layer overlying the ozone resistant barrier includes forming the top metal layer of a busline.



8. (Currently Amended) In the fabrication of liquid crystal displays (LCDs) integrated circuits (ICs), a method for forming a LCD structure resistant to ozone stripping, the method comprising:

forming an indium tin oxide (ITO) layer electrode;

forming an ozone resistant barrier overlying the electrode from a material selected from the group including Ti, Ta, TiN, and TaN; and,

forming an Al reflector overlying the ozone resistant barrier.

9. (Withdrawn) A method for stripping a liquid crystal display (LCD) surface, the method comprising:

forming a first electrically conducting layer;

forming an ozone resistive barrier overlying the first electrically conducting layer;

forming a metal layer overlying the ozonc resistive barrier;

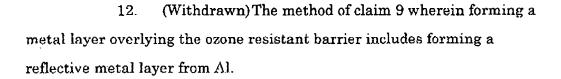
forming a photoresist pattern with openings exposing overlying areas of the metal layer;

through the openings in the photoresist, etching the exposed metal layer and underlying ozone resistant barrier; and,

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stripping the photoresist with an ozone compound.

- 10. (Withdrawn) The method of claim 9 wherein forming a first electrically conducting layer includes forming a conducting layer from indium tin oxide (ITO).
- 11. (Withdrawn) The method of claim 9 wherein forming an ozone resistant barrier overlying the first electrically conducting layer includes forming an ozone resistant barrier from a material selected from the group including Ta, Ti, TaN, TiN, Al, Al compounds, tungsten, chrome, and copper.



- 13. (Withdrawn) The method of claim 12 wherein forming a metal layer overlying the ozone resistant barrier includes forming a layer of Al having a thickness of greater than 1000 Å.
- 14. (Withdrawn) The method of claim 13 in which a reflective LCD structure is being stripped;

wherein forming a first electrically conducting layer includes forming an ITO electrode;

wherein forming an ozone resistant barrier overlying the first electrically conducting layer includes forming an ozone resistant



barrier from a material selected from the group including Ta, Ti, TaN, and TiN;

wherein forming a metal layer overlying the ozone resistant barrier includes forming an Al layer; and,

the method further comprising:

following the ozone stripping, leaving an LCD reflector structure.

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- 15. (Withdrawn) The method of claim 14 wherein stripping the photoresist with an ozone compound includes stripping with a compound having 85 parts per million (PPM) of ozone, or greater.
- 16. (Withdrawn) The method of claim 14 wherein stripping the photoresist with an ozone compound includes exposing the IC to the ozone compound for approximately 45 minutes.
- 17. (Withdrawn) The method of claim 14 wherein forming a metal layer overlying the ozone resistant barrier includes forming an Al layer having a thickness of greater than 1000 Å; and,

wherein stripping the photoresist with an ozone compound includes removing approximately 800 Å of Al exposed by the openings in the photoresist.

- 18. (Currently Amended) A liquid crystal display (LCD) reflector structure resistant to ozone stripping, the reflector structure comprising:
 - a first electrically conducting layer of indium tin oxide (ITO);



an ozone resistive barrier overlying the first electrically conducting layer from a material selected from the group including Ti. Ta.

TaN, Al. Al compounds, tungsten, and copper; and,

a metal layer overlying the ozone resistive barrier.

- 19. (Cancelled)
- 20. (Cancelled)
- 21. (Original). The reflector structure of claim 18 wherein the metal layer is a reflective metal layer material selected from the group including Al.



22. (Currently Amended) A liquid crystal display (LCD) reflector structure resistant to ozone stripping, the reflector structure comprising:

a first electrically conducting layer of indium tin oxide (ITO);
an ozone resistive barrier overlying the first electrically
conducting layer selected from the group including Ti, Ta, TiN, TaN, Al,
Al compounds, tungsten, ehrome, and copper; and,

an Al reflective metal layer overlying the ozone resistive barrier.

23. (Original) A liquid crystal display (LCD) reflector structure resistant to ozone stripping, the reflector structure comprising: a first electrically conducting layer selected from the group including Ti, Ta, and Al; and,

a reflective metal layer overlying the first electrically conducting layer selected from the group including Al.

24. (Currently Amended) In the fabrication of integrated circuit (IC) structures, a method for forming a structure resistant to ozone stripping, the method comprising:

forming a first electrically conducting layer <u>from a material</u> <u>selected from the group including Ti, Ta, and Al</u>; and,

forming a metal layer overlying the electrically conducting layer.

25. (Cancelled)

26. (Original) The method of claim 24 wherein forming a metal layer overlying the first electrically conducting layer includes forming a reflective metal layer from Al.

27. (Original) The method of claim 26 wherein forming a metal layer overlying the first electrically conducting layer includes forming a layer of Al having a thickness of greater than 1000 Å.

28. (Original) The method of claim 24 in which a reflective liquid crystal display (LCD) IC structure is formed;

wherein forming a first electrically conducting layer includes forming an electrode; and,

wherein forming a metal layer overlying the first electrically conducting layer includes forming an LCD reflector.



29. (Original) The method of claim 24 in which a busline IC structure is formed; and,

wherein forming a metal layer overlying the first electrically conducting layer includes forming the top metal layer of a busline.